#### SILICON (Si) POWER MOSFET A CEU2215



CET MOS

# **CEU2215**

# 150V ▲ 60mΩ ▲ 22A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO252 (DPAK) package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability





FREE

RoHS



Parameter ( $T_c$ = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V <sub>DS</sub>	150V
Gate-Source Voltage	V <sub>GS</sub>	±30V
Continuous Drain Current at T <sub>c</sub> = 25°C	I <sub>D</sub>	22A
Continuous Drain Current at T <sub>c</sub> = 100°C	I <sub>D</sub>	16A
Pulsed Drain Current Note 1	I <sub>DM</sub>	88A
Maximum Power Dissipation at $T_c = 25^{\circ}C$	PD	100W
Power Dissipation Derating above 25°C	ΔΡ <sub>D</sub>	0.66W/°C
Single Pulsed Avalanche Energy Note 4	E <sub>AS</sub>	3.2mJ
Single Pulsed Avalanche Current Note 4	I <sub>AS</sub>	8A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +175°C

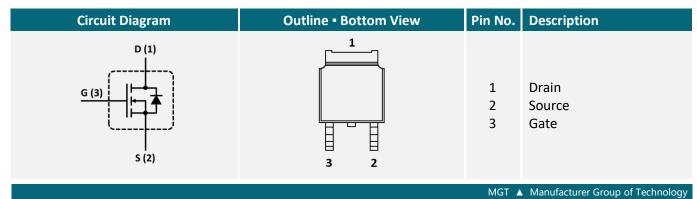
## THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1.5°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>TH_JA</sub>	50°C/W

#### **APPLICATIONS**

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
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## **PIN DESCRIPTION**



CEU2215 ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 1

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#### **ELECTRICAL CHARACTERISTICS** A T<sub>c</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	BV <sub>DSS</sub>	135	150		V
Zero Gate Voltage Drain Current	$V_{DS} = 135V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -30V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	V <sub>GS(th)</sub>	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 10A$	R <sub>DS(ON)</sub>		60	80	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 7V, I_{D} = 10A$	R <sub>DS(ON)</sub>		62	90	mΩ
Gate Resistance	f = 1MHz, Open Drain	R <sub>G</sub>		1		Ω
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS}$ = 75V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		1205		рF
Output Capacitance	$V_{DS}$ = 75V, $V_{GS}$ = 0V, f = 1MHz	Coss		105		рF
Reverse Transfer Capacitance	$V_{DS}$ = 75V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		50		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD}$ = 75V, $V_{GS}$ = 10V, $I_D$ = 10A, $R_{G(ext)}$ = 6 $\Omega$	t <sub>D(ON)</sub>		19		ns
Turn-On Rise Time	$V_{DD}$ = 75V, $V_{GS}$ = 10V, $I_D$ = 10A, $R_{G(ext)}$ = 6 $\Omega$	t <sub>R</sub>		8		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 75V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 10A, $R_{\text{G}(\text{ext})}$ = 6 $\Omega$	t <sub>D(OFF)</sub>		33		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 75V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 10A, $R_{\text{G(ext)}}$ = 6 $\Omega$	t <sub>F</sub>		6		ns
Total Gate Charge	$V_{DS}$ = 75V, $V_{GS}$ = 10V, $I_{D}$ = 10A	$Q_{G}$		27		nC
Gate Source Charge	$V_{DS}$ = 75V, $V_{GS}$ = 10V, $I_{D}$ = 10A	Q <sub>GS</sub>		5		nC
Gate Drain Charge	$V_{DS}$ = 75V, $V_{GS}$ = 10V, $I_{D}$ = 10A	$Q_{GD}$		10		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		ls			22	А
Drain-Source Diode Forward Voltage Note 2	V <sub>GS</sub> = 0V, I <sub>S</sub> = 22A	$V_{\text{SD}}$			1.2	V

#### Notes

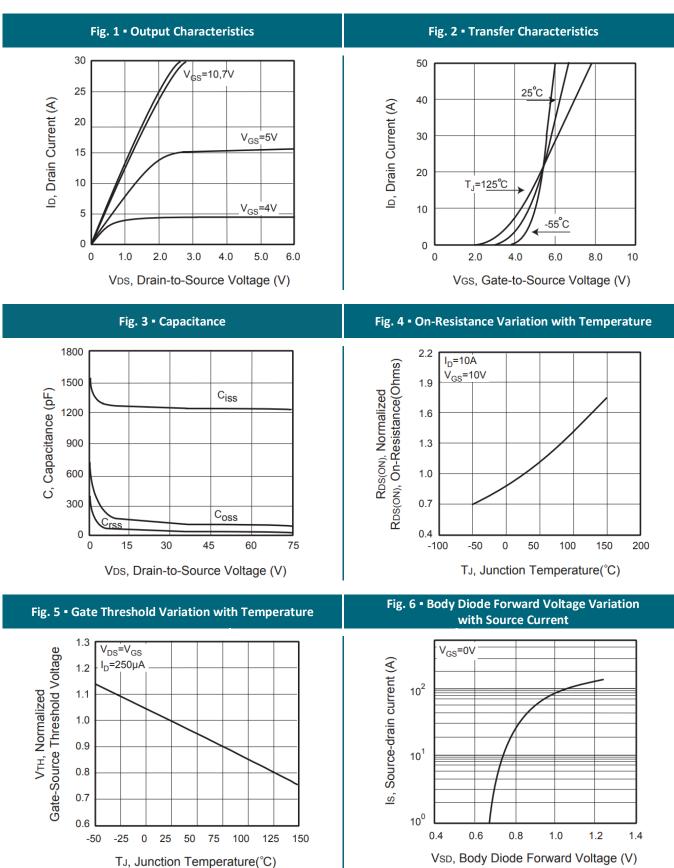
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 3: Guaranteed by design, not subject to production testing.
- 4:  $L = 0.1 \text{mH}, I_{AS} = 8 \text{A}, V_{DD} = 50 \text{V}, R_G = 25 \Omega, \text{ Starting } T_J = 25^{\circ}\text{C}$



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## **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**

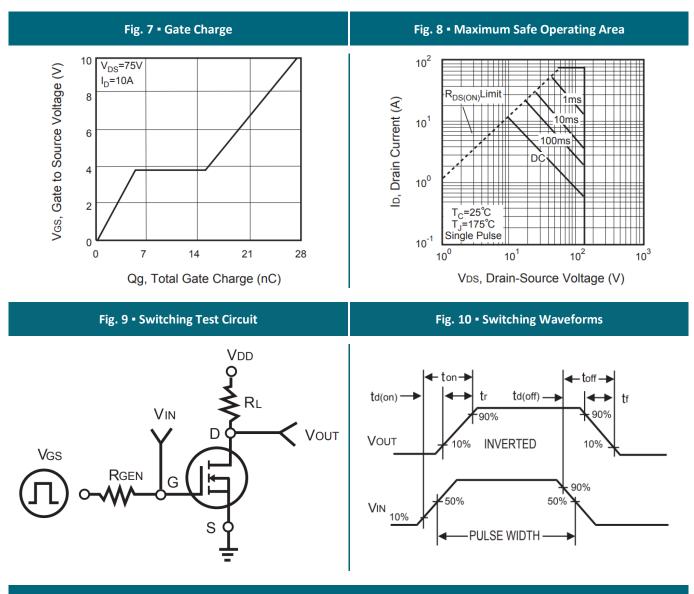


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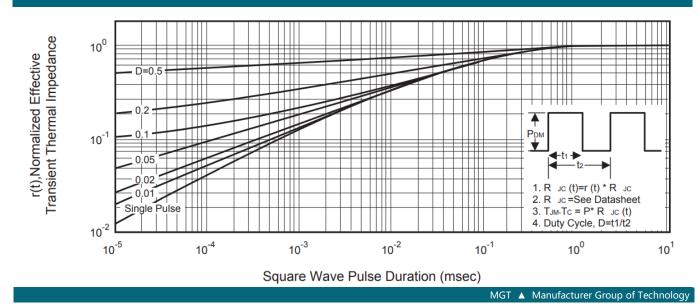


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## **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



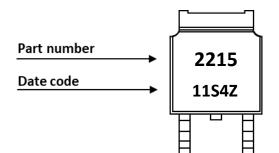
#### Fig. 11 • Normalized Thermal Transient Impedance Curve



#### SILICON (Si) POWER MOSFET ▲ CEU2215

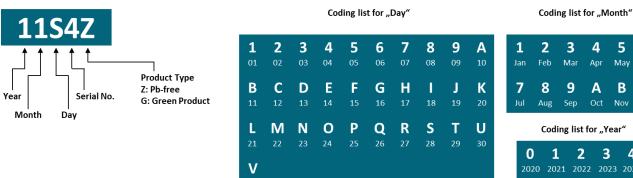
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#### **DATE CODE**

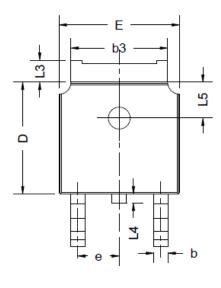
Example: 11S4Z

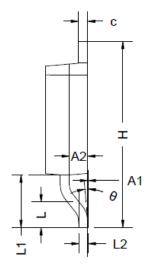


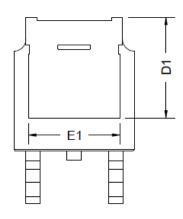
5 6 С В Coding list for "Year" 4 5 9 6 7 8



#### **PACKAGE OUTLINE**







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Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	2.20	2.30	2.38	е		2.286 BSC	
A1	0.00	-	0.20	Н	9.40	10.10	10.50
A2	0.90	1.07	1.17	L	1.38	1.50	1.75
b	0.68	0.78	0.90	L1		2.90 REF	
b3	5.23	5.33	5.46	L2		0.51 BSC	
С	0.43	0.53	0.61	L3	0.88	-	1.28
D	5.98	6.10	6.22	L4	0.50		1.00
D1		5.30 REF		L5	1.65	1.80	1.95
E	6.40	6.60	6.73	θ	0°	-	8°
E1	4.63	-	-				

#### **ORDERING INFORMATION**

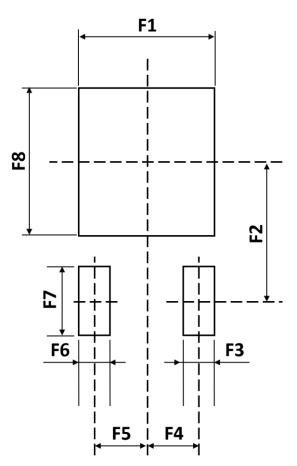
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEU2215	TO252 (DPAK)	Reel	2,500pcs	5,000pcs	40,000pcs

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## **RECOMMENDED PAD LAYOUT**



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-	F5	-	2.29	-
F2	-	6.25	-	F6	-	1.40	-
F3	-	1.40	-	F7	-	3.00	-
F4	-	2.29	-	F8	-	6.50	-

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

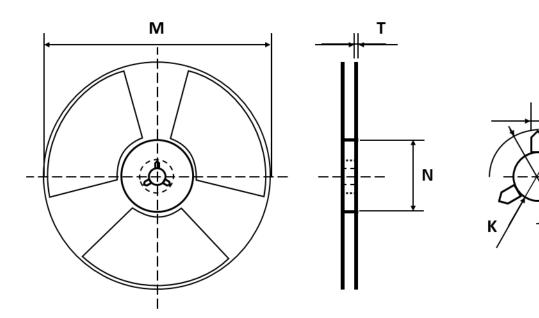


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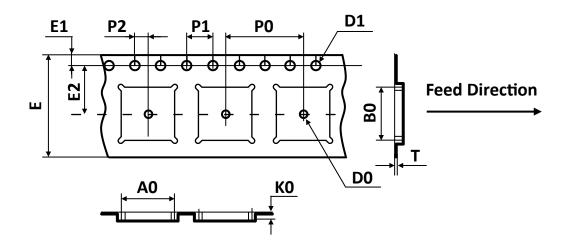


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	Т	Н	К	S
	Ø330	Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
16mm		±2.00	±0.50	+0.20	+0 50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

# TAPE DIMENSIONS All dimensions in mm

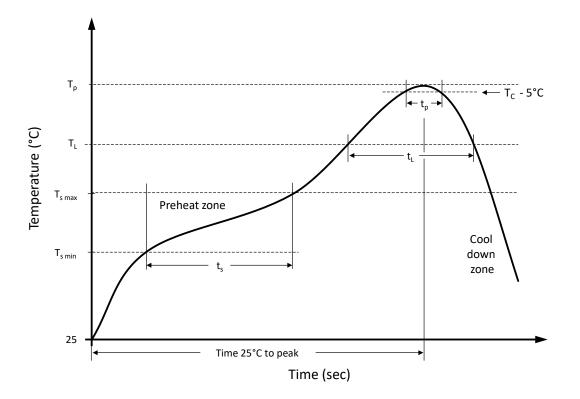


Package	A0	B0	КО	D0	D1	E	E1	E2	P0	P1	P2	т
TO252	6.90	10.50	2.70	1.50	1.50	16.00	1.75	7.50	8.00	4.00	2.00	0.30
(DPAK)	±0.10	±0.10	±0.10	MIN	±0.10	+0.30 -0.20	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05





#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{smax}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	tL	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



## **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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